

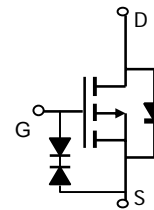
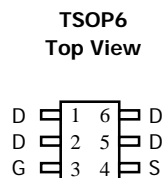
**AO6415**
**P-Channel Enhancement Mode Field Effect Transistor**

**General Description**

The AO6415 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected. *Standard Product AO6415 is Pb-free (meets ROHS & Sony 259 specifications). AO6415L is a Green Product ordering option. AO6415 and AO6415L are electrically identical.*

**Features**

$V_{DS} (V) = -20V$   
 $I_D = -3.3A (V_{GS} = -10V)$   
 $R_{DS(ON)} < 75m\Omega (V_{GS} = -10V)$   
 $R_{DS(ON)} < 100m\Omega (V_{GS} = -4.5V)$   
 $R_{DS(ON)} < 150m\Omega (V_{GS} = -2.5V)$   
 ESD Rating: 2000V HBM


**Absolute Maximum Ratings  $T_A=25^\circ C$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current <sup>A</sup>	$T_A=25^\circ C$ $T_A=70^\circ C$	$I_D$	A
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	-14	
Power Dissipation <sup>A</sup>	$T_A=25^\circ C$ $T_A=70^\circ C$	$P_D$	W
		0.8	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ C$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	82	100	$^\circ C/W$
$t \leq 10s$				
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JL}$	56	70	$^\circ C/W$
Steady-State				
Maximum Junction-to-Lead <sup>C</sup>				

Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}$ , $V_{GS}=0\text{V}$	-20			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-16\text{V}$ , $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$		-0.003	-0.5 -2.5	$\mu\text{A}$
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 10\text{V}$			$\pm 1$	$\mu\text{A}$
		$V_{DS}=0\text{V}$ , $V_{GS}=\pm 12\text{V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=-250\mu\text{A}$	-0.6	-0.9	-1.4	
$I_{D(ON)}$	On state drain current	$V_{GS}=-4.5\text{V}$ , $V_{DS}=-5\text{V}$	-20			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}$ , $I_D=-3.3\text{A}$ $T_J=125^\circ\text{C}$		62 84	75 105	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}$ , $I_D=-2\text{A}$		80	100	$\text{m}\Omega$
		$V_{GS}=-2.5\text{V}$ , $I_D=-1\text{A}$		115	150	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=-5\text{V}$ , $I_D=-3.3\text{A}$		7		S
$V_{SD}$	Diode Forward Voltage	$I_S=-1\text{A}$ , $V_{GS}=0\text{V}$	-0.65	-0.82	-1	V
$I_S$	Maximum Body-Diode Continuous Current				-1.5	A
<b>DYNAMIC PARAMETERS</b>						
$C_{ISS}$	Input Capacitance			512	620	pF
$C_{OSS}$	Output Capacitance	$V_{GS}=0\text{V}$ , $V_{DS}=-10\text{V}$ , $f=1\text{MHz}$		77		pF
$C_{RSS}$	Reverse Transfer Capacitance			62		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$		9.2	13	$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g$	Total Gate Charge			4.9	6	nC
$Q_{gs}$	Gate Source Charge	$V_{GS}=-4.5\text{V}$ , $V_{DS}=-10\text{V}$ , $I_D=-2\text{A}$		0.8		nC
$Q_{gd}$	Gate Drain Charge			1.2		nC
$t_{D(on)}$	Turn-On DelayTime			11	13	ns
$t_r$	Turn-On Rise Time	$V_{GS}=-4.5\text{V}$ , $V_{DS}=-10\text{V}$ , $R_L=5\Omega$ ,		8	10	ns
$t_{D(off)}$	Turn-Off DelayTime	$R_{GEN}=3\Omega$		34	41	ns
$t_f$	Turn-Off Fall Time			12	15	ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=-2\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		13	17	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=-2\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		4	6	nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 $\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

Rev 0 : Nov 2005

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

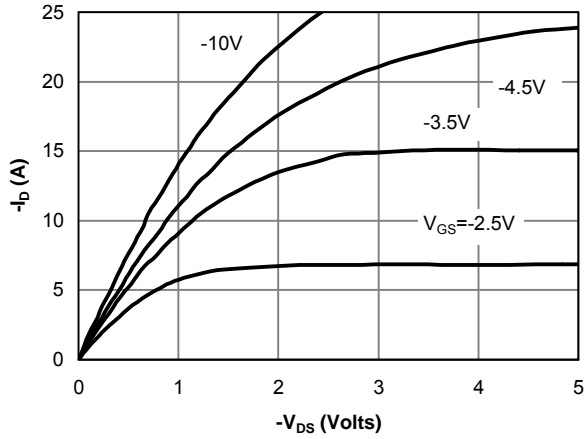


Fig 1: On-Region Characteristics

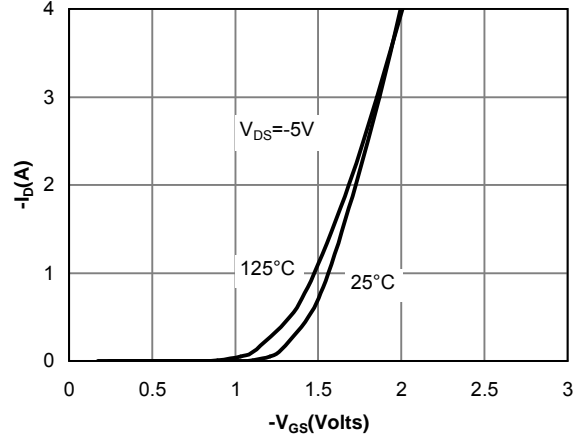


Figure 2: Transfer Characteristics

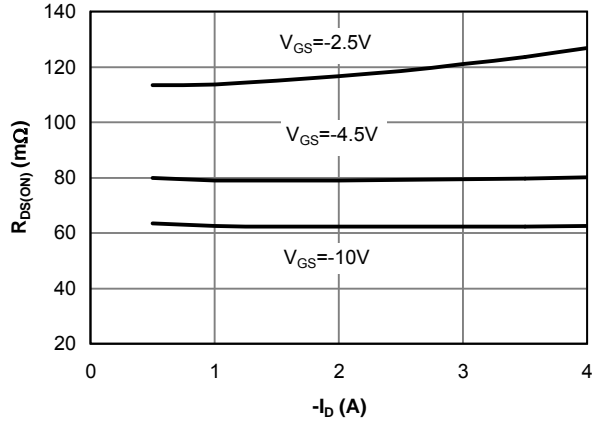


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

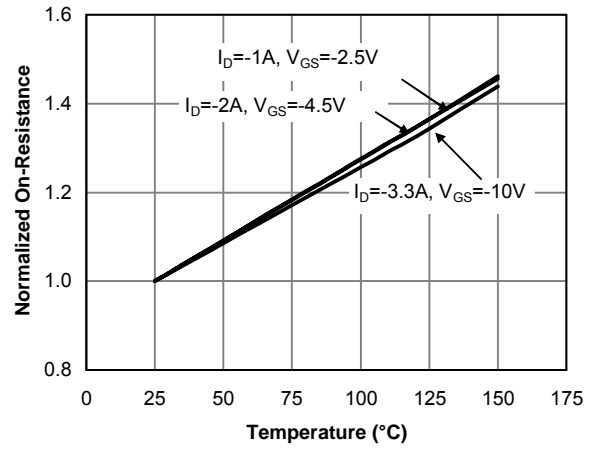


Figure 4: On-Resistance vs. Junction Temperature

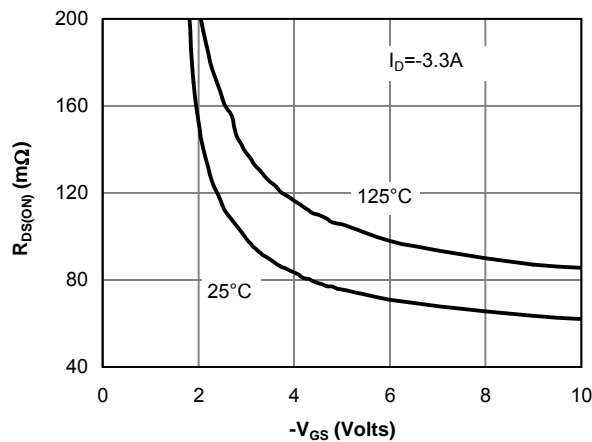


Figure 5: On-Resistance vs. Gate-Source Voltage

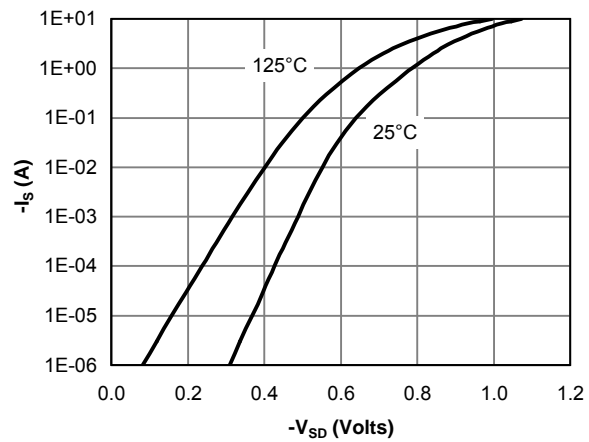


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

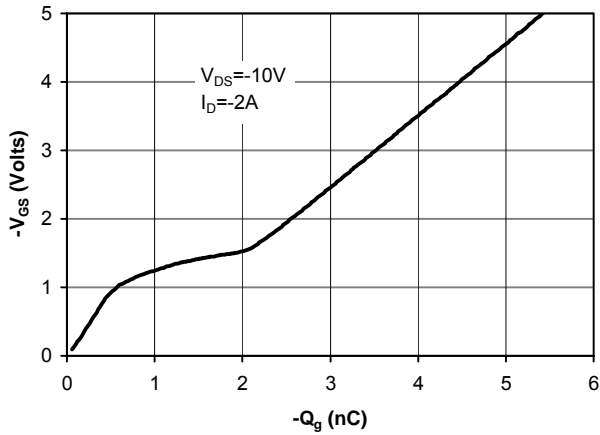


Figure 7: Gate-Charge Characteristics

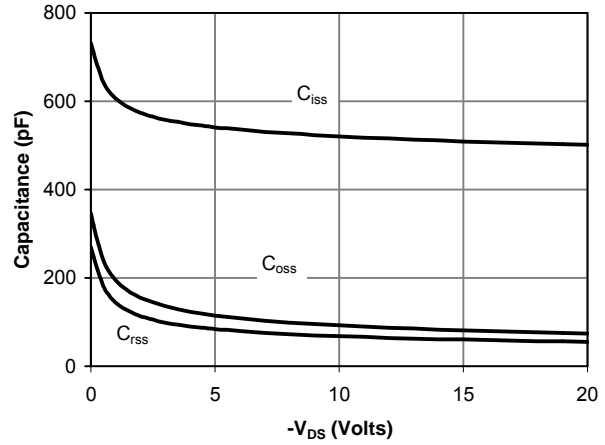


Figure 8: Capacitance Characteristics

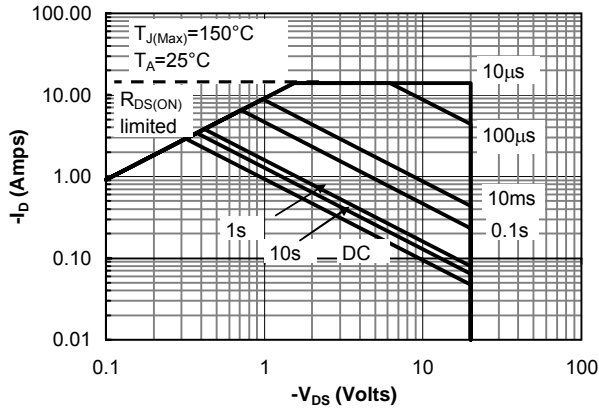


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

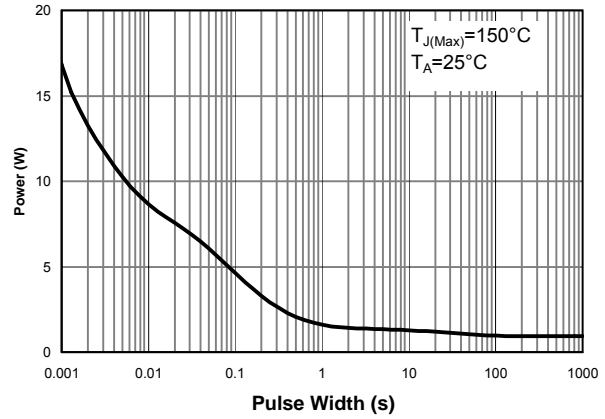


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

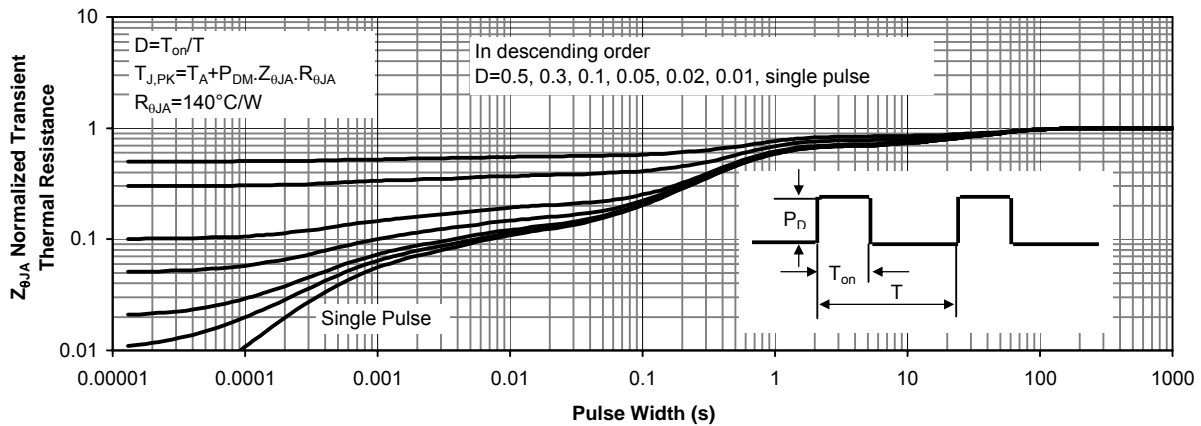


Figure 11: Normalized Maximum Transient Thermal Impedance